## IN THE CLAIMS

- 1. (Canceled)
- 2. (currently amended) A system for processing a semiconductor device, the system comprising:
  - a processing chamber heated by heating elements; and
- a first plate positioned within said processing chamber and defining a first internal cavity configured to receive a first gas through a first passage into said first internal cavity at a first temperature and to emit said first gas from said first internal cavity at a second temperature through a second passage; and

a second plate disposed adjacent to said first plate, said first plate and said second plate provided between said heating elements and defining a processing area therebetween, said second plate defining a second internal cavity configured to receive a second gas through a first passage into said second internal cavity at a first temperature and to emit said second gas from said second internal cavity at a second temperature through a second passage, said first emitted gas and said second emitted gas varying the temperature of said processing area.

- (currently amended) The system of Claim 2, wherein said second passage comprise comprises a plurality of holes defined on a surface of said first and said second plates.
- 4. (previously presented) The system of Claim 2, wherein said first plate and said second plate comprise a heat source for heating said plate to a preselected temperature.
- 5. (previously presented) The system of Claim 2, wherein said first gas is taken from the group consisting of N<sub>2</sub>, He, H<sub>2</sub>, O<sub>2</sub>, Ar and gas mixtures containing He, H<sub>2</sub>, O<sub>2</sub>, Ar and N<sub>2</sub>.
- 6. (previously presented) The system of Claim 2, wherein said internal cavity further comprises a buffer to disperse said first gas throughout said internal cavity.
  - 7. (canceled)

LAW OFFICES OF MACPHERSON KWOK CHEN A BEID LLF

2403 MICHELSON DRIVE SLITE 210 IRVINE, CA 92612 (949) 752-7040 FAX (949) 752-7049

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- 8. (currently amended) A system for wafer processing comprising: a chamber <u>heated by heating elements</u>; and
- a first heatable plate and a second heatable plate positioned between said heating elements within said chamber, and defining a processing area therebetween, each of said heatable plates including:

an internal cavity defining an internal wall and configured to receive a gas; means for heating said internal wall to a preselected temperature; and an outlet portion defining a plurality of holes for emitting said gas to said processing area;

said gas varying the temperature of said processing area.

- 9. (previously presented) The system of Claim 8, wherein said gas is taken from the group consisting of He, H<sub>2</sub>, O<sub>2</sub>, Ar, N<sub>2</sub> and gas mixtures containing He, H<sub>2</sub>, O<sub>2</sub>, Ar, and N<sub>2</sub>.
- 10. (previously presented) The system of Claim 8, wherein said internal cavity further comprises a buffer to disperse said first gas throughout said internal cavity.

11.-16. (canceled)

PARTO HAND WALL HARD MOERAHYOAN HEED LLD

> 402 MICHELSON DRIVE SUITB 210 (RYD/B. CA 92613 (949) 752-7040 PAY (949) 753-7040

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